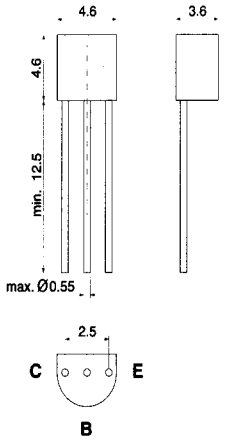
PNP Silicon Expitaxial Planar Transistor
for switching and amplifier applications. Especially suitable for AF-driver stages and low-power output stages.

These types are also available subdivided into three groups -16, -25 and -40, according to their DC current gain. As complementary types, the NPN transistors BC337 and BC338 are recommended.

On special request, these transistors can be manufactured in different pin configurations. Please refer to the "TO-92 TRANSISTOR PACKAGE OUTLINE" on page 80 for the available pin options.



TO-92 Plastic Package
Weight approx. 0.18 g
Dimensions in mm

Absolute Maximum Ratings (T_a = 25°C)

		Symbol	Value	Unit
Collector Emitter Voltage	**HN / BC 327**	$-V_{CES}$	50	V
	HN / BC 328	$-V_{CES}$	30	V
Collector Emitter Voltage	**HN / BC 327**	$-V_{CEO}$	45	V
	HN / BC 328	$-V_{CEO}$	25	V
Emitter Base Voltage		$-V_{EBO}$	5	V
Collector Current		$-I_C$	800	mA
Peak Collector Current		$-I_{CM}$	1	A
Base Current		$-I_B$	100	mA
Power Dissipation at T_{amb} = 25 °C		P_{tot}	625[1)]	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_s	-65 to + 150	°C

[1)] Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

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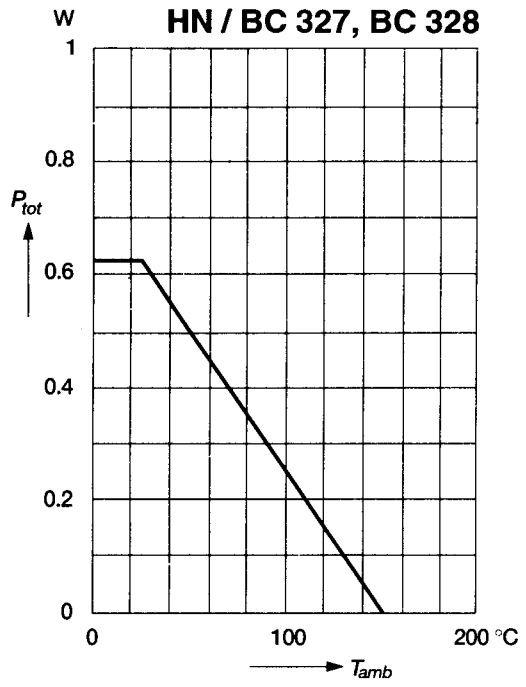
Characteristics at T_{amb} =25 °C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain.						
at $-V_{CE}$ = 1V, $-I_C$ = 300 mA						
	Current Gain Group-16	h_{FE}	100	160	250	-
	-25	h_{FE}	160	250	400	-
	-40	h_{FE}	250	400	630	-
at $-V_{CE}$ = 1V, $-I_C$ = 300 mA						
	Current Gain Group-16	h_{FE}	60	130	-	-
	-25	h_{FE}	100	200	-	-
	-40	h_{FE}	170	320	-	-
Thermal Resistance Junction to Ambient Air		R_{thA}	-	-	200[1)]	K/W
Collector Emitter Cutoff Current						
at $-V_{CE}$ = 45 V	**HN / BC 327**	$-I_{CES}$	-	2	100	nA
at $-V_{CE}$ = 25 V	**HN / BC 328**	$-I_{CES}$	-	2	100	nA
at $-V_{CE}$ = 45 V, T_{amb} = 125 °C	**HN / BC 327**	$-I_{CES}$	-	-	10	µA
at $-V_{CE}$ = 25 V, T_{amb} = 125 °C	**HN / BC 328**	$-I_{CES}$	-	-	10	µA
Collector Emitter Breakdown Voltage						
at $-I_C$ = 10 mA	**HN / BC 327**	$-V_{(BR)CEO}$	45	-	-	V
	HN / BC 328	$-V_{(BR)CEO}$	25	-	-	V
Collector Emitter Breakdown Voltage						
at $-I_C$ = 0.1 mA	**HN / BC 327**	$-V_{(BR)CES}$	50	-	-	V
	HN / BC 328	$-V_{(BR)CES}$	30	-	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 0.1 mA		$-V_{(BR)EBO}$	5	-	-	V
Collector Saturation Voltage at $-I_C$ = 500 mA, $-I_B$ = 50 mA		$-V_{CEsat}$	-	-	0.7	V
Base Emitter Voltage at $-V_{CE}$ = 1 V, $-I_C$ = 300 mA		$-V_{BE}$	-	-	1.2	V
Gain Bandwidth Product at $-V_{CE}$ = 5V, $-I_C$ = 10 mA, f = 50MHz		f_T	-	100	-	MHz
Collector Base Capacitance at $-V_{CB}$ = 10 V, f = 1MHz		C_{CBO}	-	12	-	pF

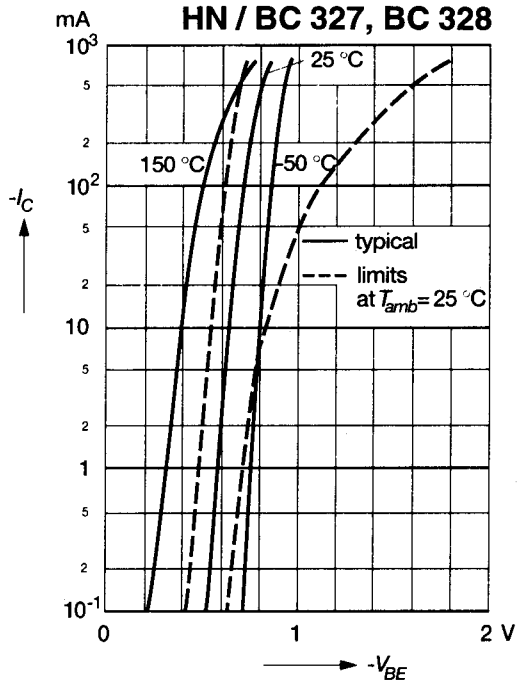
[1)] Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

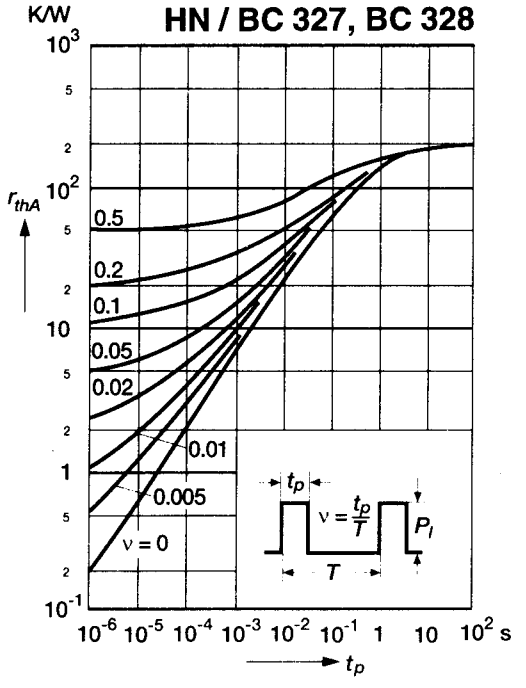


Collector current versus base-emitter voltage

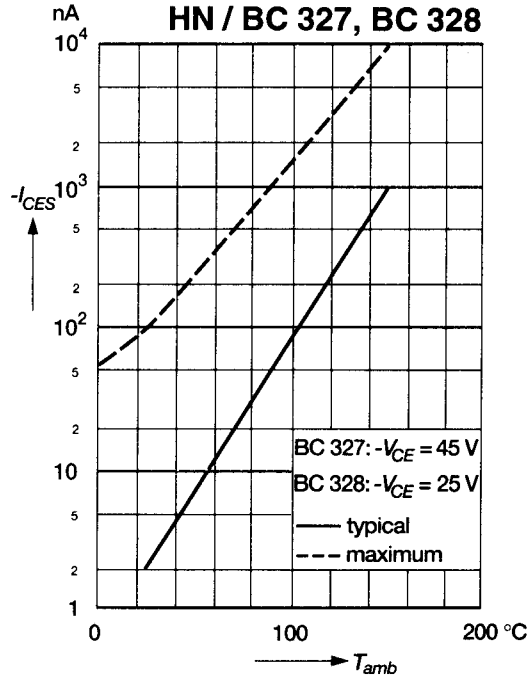


Pulse thermal resistance versus pulse duration

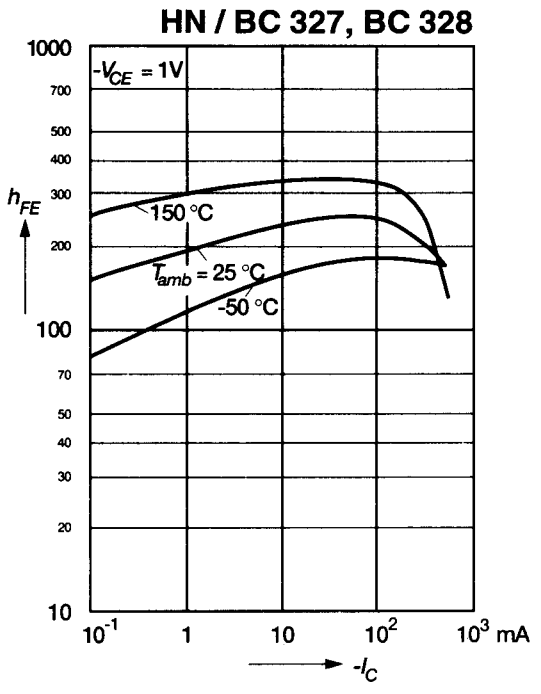
Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case



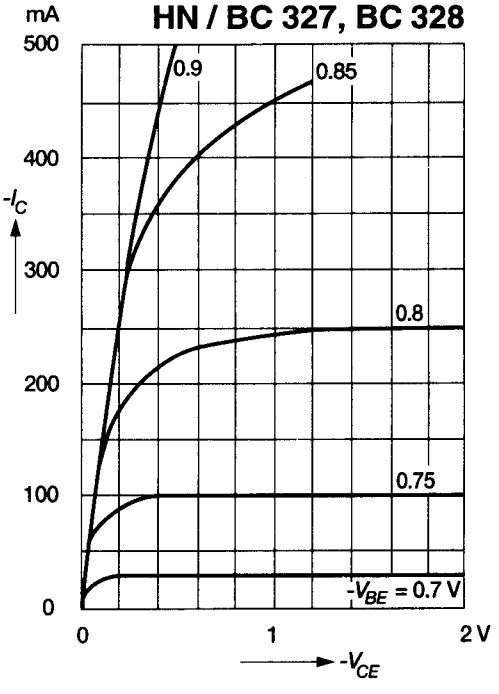
Collector-emitter cutoff current versus ambient temperature



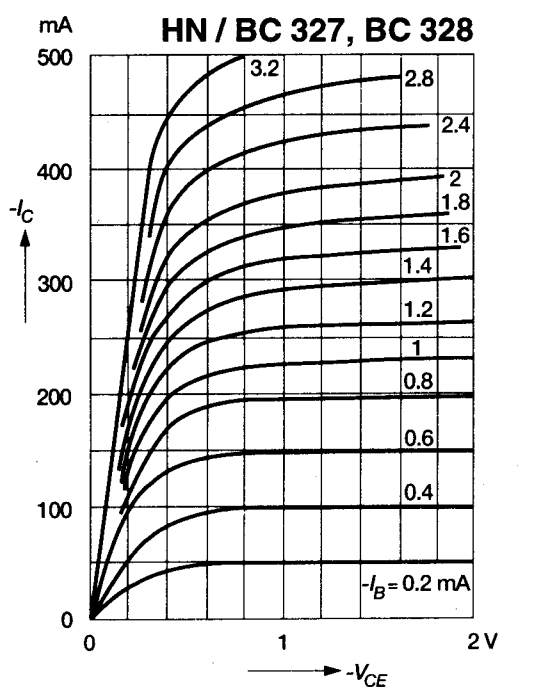
DC current gain versus collector current



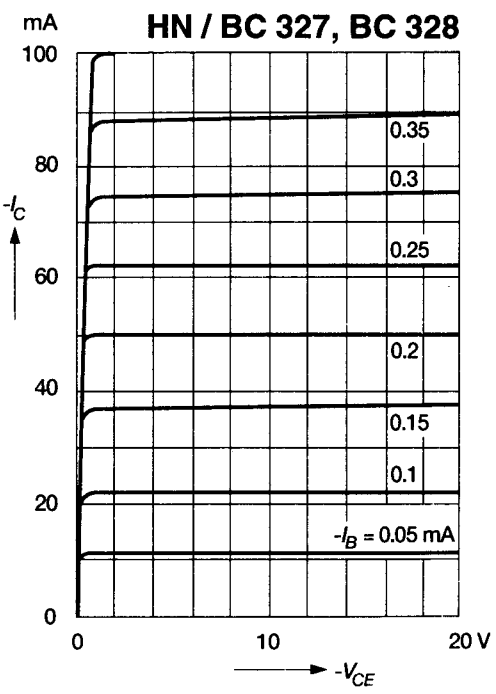
Common emitter collector characteristics



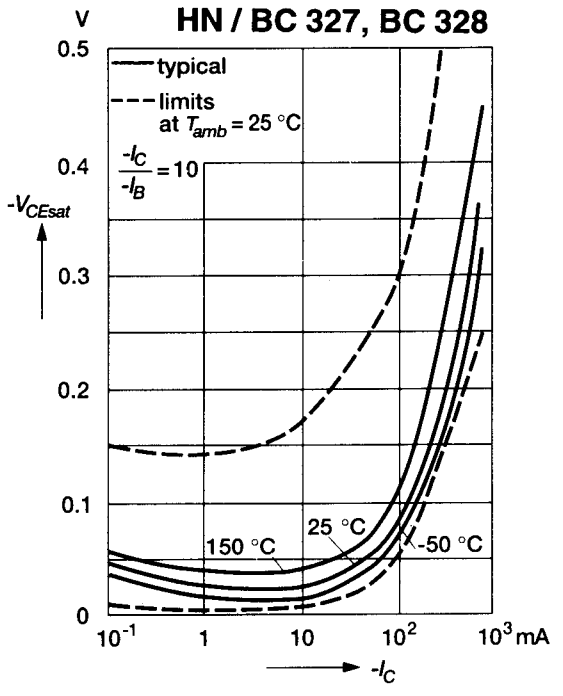
Common emitter collector characteristics



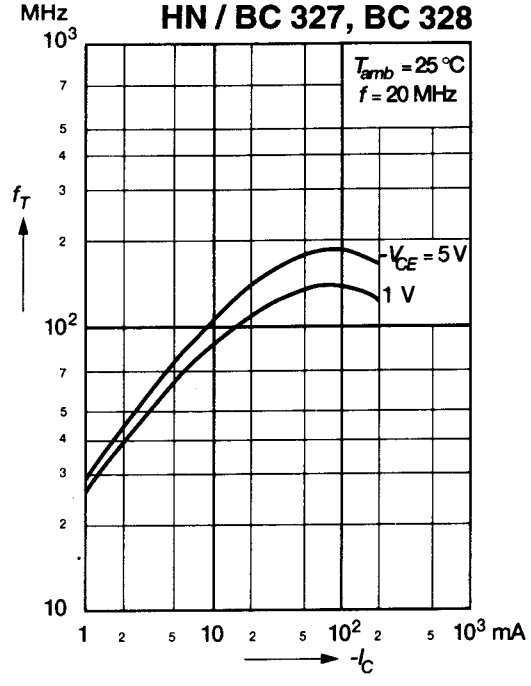
Common emitter collector characteristics



Collector saturation voltage versus collector current



Gain-bandwidth product versus collector current



Base saturation voltage versus collector current